Features

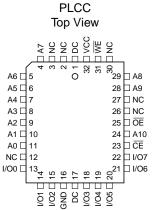
- Fast Read Access Time 150 ns
- Fast Byte Write 200 µs or 1 ms
- Self-Timed Byte Write Cycle
 - Internal Address and Data Latches
 - Internal Control Timer
 - Automatic Clear Before Write
- Direct Microprocessor Control
 - DATA POLLING
- Low Power
 - 30 mA Active Current
 - 100 µA CMOS Standby Current
- High Reliability
 - Endurance: 10⁴ or 10⁵ Cycles
 - Data Retention: 10 Years
- 5V ± 10% Supply
- CMOS & TTL Compatible Inputs and Outputs
- JEDEC Approved Byte Wide Pinout
- Commercial and Industrial Temperature Ranges

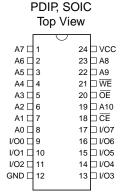
Description

The AT28C16 is a low-power, high-performance Electrically Erasable and Programmable Read Only Memory with easy to use features. The AT28C16 is a 16K memory organized as 2,048 words by 8 bits. The device is manufactured with Atmel's reliable nonvolatile CMOS technology. *(continued)*

Pin Configurations

Pin Name	Function
A0 - A10	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect
DC	Don't Connect







16K (2K x 8) Parallel EEPROMs

AT28C16

Rev. 0540B-10/98



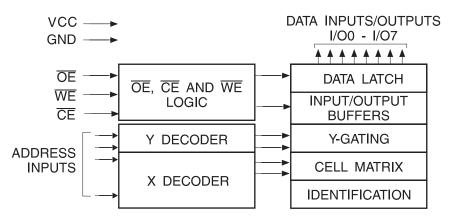


The AT28C16 is accessed like a static RAM for the read or write cycles without the need of external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The end of a write cycle can be determined by DATA POLLING of I/O₇. Once the end of a write cycle has been detected, a new access for a read or a write can begin.

The CMOS technology offers fast access times of 150 ns at low power dissipation. When the chip is deselected the standby current is less than 100 μ A.

Atmel's 28C16 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32 bytes of EEPROM are available for device identification or tracking.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including NC Pins) with Respect to Ground0.6V to +6.25V
All Output Voltages with Respect to Ground0.6V to V _{CC} + 0.6V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground0.6V to +13.5V

*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

Device Operation

READ: The AT28C16 is accessed like a Static RAM. When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever \overline{CE} or \overline{OE} is high. This dual line control gives designers increased flexibility in preventing bus contention.

BYTE WRITE: Writing data into the AT28C16 is similar to writing into a Static RAM. A low pulse on the \overline{WE} or \overline{CE} input with \overline{OE} high and \overline{CE} or \overline{WE} low (respectively) initiates a byte write. The address location is latched on the last falling edge of \overline{WE} (or \overline{CE}); the new data is latched on the first rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of t_{WC} , a read operation will effectively be a polling operation.

FAST BYTE WRITE: The AT28C16E offers a byte write time of 200 μ s maximum. This feature allows the entire device to be rewritten in 0.4 seconds.

DATA POLLING: The AT28C16 provides DATA POLLING to signal the completion of a write cycle. During a write

cycle, an attempted read of the data being written results in the complement of that data for I/O_7 (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

WRITE PROTECTION: Inadvertent writes to the device are protected against in the following ways: (a) V_{CC} sense—if V_{CC} is below 3.8V (typical) the write function is inhibited; (b) V_{CC} power on delay—once V_{CC} has reached 3.8V the device will automatically time out 5 ms (typical) before allowing a byte write; and (c) write inhibit—holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits byte write cycles.

CHIP CLEAR: The contents of the entire memory of the AT28C16 may be set to the high state by the CHIP CLEAR operation. By setting $\overline{\text{CE}}$ low and $\overline{\text{OE}}$ to 12 volts, the chip is cleared when a 10 msec low pulse is applied to $\overline{\text{WE}}$.

DEVICE IDENTIFICATION: An extra 32 bytes of EEPROM memory are available to the user for device identification. By raising A9 to 12 ± 0.5 V and using address locations 7E0H to 7FFH the additional bytes may be written to or read from in the same manner as the regular memory array.





DC and AC Operating Range

		AT28C16-15
Operating Temperature (Case)	Com.	0°C - 70°C
	Ind.	-40°C - 85°C
V _{CC} Power Supply		5V ± 10%

Operating Modes

Mode	CE	ŌĒ	WE	I/O
Read	V_{IL}	V _{IL}	V _{IH}	D _{OUT}
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	D _{IN}
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	Х	High Z
Write Inhibit	Х	X	V _{IH}	
Write Inhibit	Х	V _{IL}	Х	
Output Disable	Х	V _{IH}	Х	High Z
Chip Erase	V _{IL}	V _H ⁽³⁾	V _{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH} .

2. Refer to AC Programming Waveforms.

3. $V_H = 12.0V \pm 0.5V$

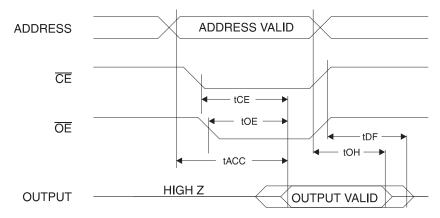
DC Characteristics

Symbol	Parameter	Condition		Min	Max	Units
I _{LI}	Input Load Current	$V_{IN} = 0V \text{ to } V_{CC} + 1V$			10	μΑ
I _{LO}	Output Leakage Current	$V_{I/O} = 0V \text{ to } V_{CC}$			10	μΑ
I _{SB1}	V _{CC} Standby Current CMOS	$\overline{\text{CE}} = \text{V}_{\text{CC}} - 0.3 \text{V to V}_{\text{CC}} + 1.$	OV		100	μΑ
	V Standby Current TTI	$\overline{CE} = 2.0 \text{V to V}_{CC} + 1.0 \text{V}$	Com.		2	mA
I _{SB2}	I _{SB2} V _{CC} Standby Current TTL		Ind.		3	mA
	V Active Comment AC	$f = 5 \text{ MHz}; I_{OUT} = 0 \text{ mA}$ $\overline{CE} = V_{IL}$	Com.		30	mA
I _{CC}	V _{CC} Active Current AC		Ind.		45	mA
V _{IL}	Input Low Voltage				0.8	V
V _{IH}	Input High Voltage			2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA			.4	V
V _{OH}	Output High Voltage	Ι _{ΟΗ} = -400 μΑ		2.4		V

AC Read Characteristics

		AT28C16-15		
Symbol	Parameter	Min	Max	Units
t _{ACC}	Address to Output Delay		150	ns
t _{CE} ⁽¹⁾	CE to Output Delay		150	ns
t _{OE} ⁽²⁾	OE to Output Delay	10	70	ns
t _{DF} ⁽³⁾⁽⁴⁾	CE or OE High to Output Float	0	50	ns
t _{OH}	Output Hold from OE, CE or Address, whichever occurred first	0		ns

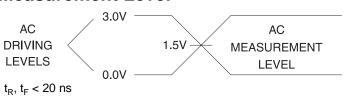
AC Read Waveforms⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾



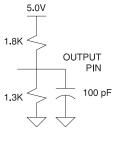
Notes: 1. $\overline{\text{CE}}$ may be delayed up to t_{ACC} - t_{CE} after the address transition without impact on t_{ACC} .

- 2. $\overline{\text{OE}}$ may be delayed up to t_{CE} t_{OE} after the falling edge of $\overline{\text{CE}}$ without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC} .
- 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
- 4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load



Pin Capacitance

 $f = 1 \text{ MHz}, T = 25^{\circ}C^{(1)}$

Symbol	Тур	Max	Units	Conditions
C _{IN}	4	6	pF	V _{IN} = 0V
C _{OUT}	8	12	pF	V _{OUT} = 0V

Note: 1. This parameter is characterized and is not 100% tested.



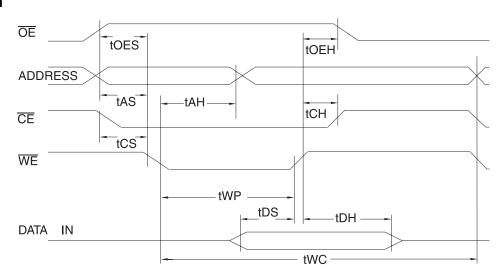


AC Write Characteristics

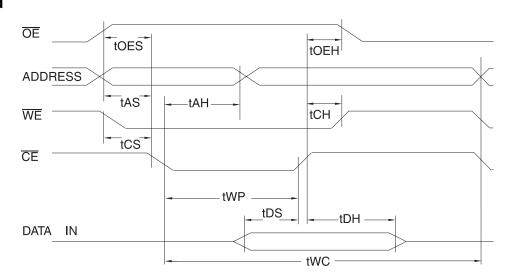
Symbol	Parameter	Min	Тур	Max	Units	
t _{AS} , t _{OES}	Address, OE Set-up Time		10			ns
t _{AH}	Address Hold Time		50			ns
t _{WP}	Write Pulse Width (WE or CE)		100		1000	ns
t _{DS}	Data Set-up Time	50			ns	
t _{DH} , t _{OEH}	Data, OE Hold Time		10			ns
t _{CS} , t _{CH}	CE to WE and WE to CE Set-up and Hold Time		0			ns
	Marita Cuala Tima	AT28C16		0.5	1.0	ms
t _{WC}	Write Cycle Time AT28C16E			100	200	μs

AC Write Waveforms

WE Controlled



CE Controlled



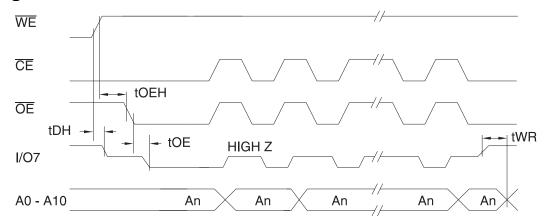
Data Polling Characteristics⁽¹⁾

Symbol	Parameter	Min	Тур	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	OE Hold Time	10			ns
t _{OE}	OE to Output Delay ⁽²⁾				ns
t _{WR}	Write Recovery Time	0			ns

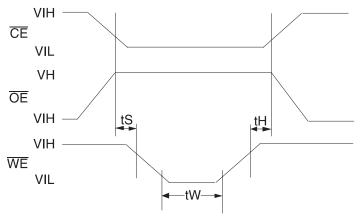
Notes: 1. These parameters are characterized and not 100% tested.

2. See AC Characteristics.

Data Polling Waveforms



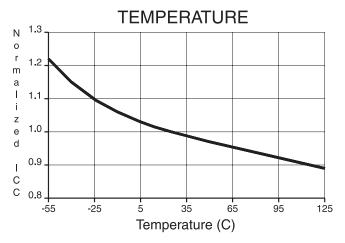
Chip Erase Waveforms



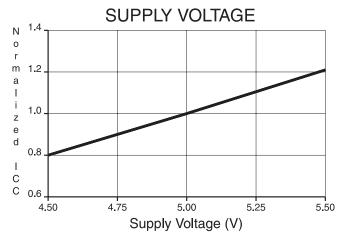
$$\begin{split} t_S &= t_H = 1 \; \mu \text{sec (min.)} \\ t_W &= 10 \; \text{msec (min.)} \\ V_H &= 12.0 V \pm 0.5 V \end{split}$$



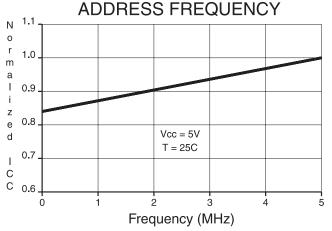
NORMALIZED SUPPLY CURRENT vs.



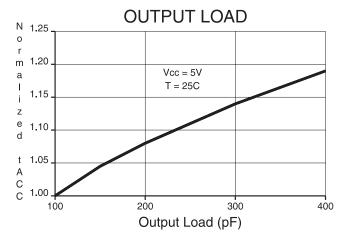
NORMALIZED SUPPLY CURRENT vs.



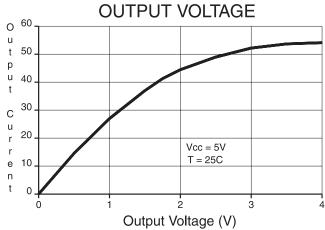
NORMALIZED SUPPLY CURRENT vs.



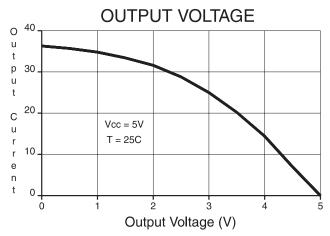
NORMALIZED ACCESS TIME vs.



OUTPUT SINK CURRENT vs.



OUTPUT SOURCE CURRENT vs.



Ordering Information⁽¹⁾

t _{ACC}	I _{CC} (mA)				
(ns)	Active	Standby	Ordering Code	Package	Operation Range
150	30	0.1	AT28C16(E)-15JC	32J	Commercial
			AT28C16(E)-15PC	24P6	(0°C to 70°C)
			AT28C16(E)-15SC	24S	
	45	0.1	AT28C16(E)-15JI	32J	Industrial
			AT28C16(E)-15PI	24P6	(-40°C to 85°C)
			AT28C16(E)-15SI	24S	

- Notes: 1. See Valid Part Numbers table below.
 - 2. The 28C16 200 ns and 250 ns speed selections have been removed from valid selections table and are replaced by the faster 150 ns T_{AA} offering.
 - 3. The 28C16 ceramic package offerings have been removed. New designs should utilize the 28C256 ceramic offerings.

Valid Part Numbers

The following table lists standard Atmel products that can be ordered.

Device Numbers Speed Package and Temperature Combinations		
AT28C16	15	JC, JI, PC, PI, SC, SI
AT28C16E	15	JC, JI, PC, PI, SC, SI
AT28C16	-	W

Die Products

Reference Section: Parallel EEPROM Die Products

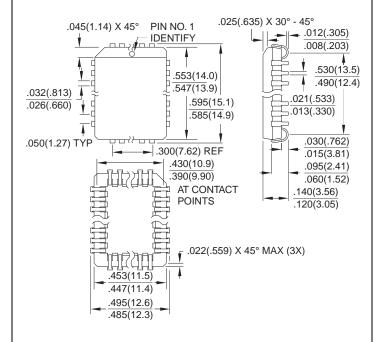
	Package Type				
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)				
24P6	24P6 24 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)				
24S	24S 24 Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)				
W	Die				
	Options				
Blank	Blank Standard Device: Endurance = 10K Write Cycles; Write Time = 1 ms				
E	High Endurance Option: Endurance = 100K Write Cycles; Write Time = 200 μs				





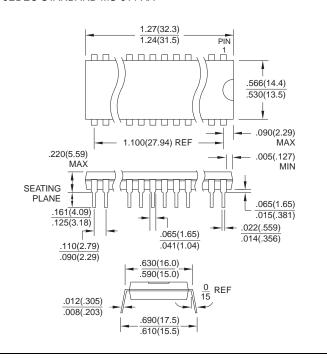
Packaging Information

32J, 32-Lead, Plastic J-Leaded Chip Carrier (PLCC) Dimensions in Inches and (Millimeters)
JEDEC STANDARD MS-018 AA



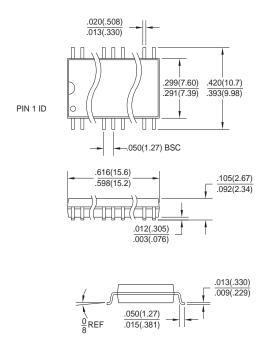
24P6, 24-Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)

Dimensions in Inches and (Millimeters) JEDEC STANDARD MS-011 AA



24S, 24-Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)

Dimensions in Inches and (Millimeters)







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